

Amendments to the Specification:

Please replace the paragraph beginning on page 20, line 16 with the following amended paragraph:

Additionally, since each of these multicomponent oxide materials is based on combination of groups 12 and 13 cations, a substantial degree of qualitative similarity is expected in structural and electrical properties, and in processing considerations. Furthermore, zinc-indium oxide, a constituent of the two-component oxides disclosed herein has been shown to exhibit excellent electron transport and thus, qualitatively similar performance from the remaining two-component oxide combinations including the three, and four-component oxides can be expected. An example of the electron transport characteristics of the zinc-indium oxide can be found in copending U.S. Patent Application Serial No. [[_____]] 10/799,961 entitled "SEMICONDUCTOR DEVICE" filed on [[_____]] March 12, 2004.

Abstract

Please replace the Abstract with the following replacement Abstract:

One exemplary embodiment includes a semiconductor device. The semiconductor device ~~can include~~ comprising a channel including one or more of a metal oxide including zinc-gallium, cadmium-gallium, cadmium-indium.